

N-Channel Enhancement Mode Field Effect Transistor

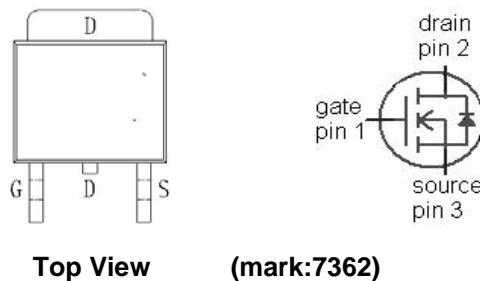
- Features

- N-channel, normal leve
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC for target application
- Ideal for high-frequency switching and synchronous rectification

- Product Summary

V_{DS}	V_{GS}	Test Conditions	$R_{DS(on)}$
60V	$\pm 20V$	5.5A@ $V_{GS}=10V$	30mR
		4.5A@ $V_{GS}=4V5$	35mR

- Pin Configurations(TO252)



- Absolute Maximum Ratings TA=25°C unless otherwise noted

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	Continuous I_D	6 ^(1A) 26 ^(1B)	A
	Pulse I_{DM}	80	
Total Power Dissipation ^(note1)	P_D	2.5 ^(1A)	W
		50 ^(1B)	
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes

1A、Surface Mounted on 1x1FR4 Board.

1B、Pulse width limited maximum junction temperature Pulse test: PW≤300 us duty cycle ≤2%

- The value of PD is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25° C. The value in any given application depends on the user's specific board design. The current rating is based on the DC thermal resistance rating and PCB layout: A. Minimum footprint; B. With additional heat sink.
- Repetitive rating, pulse width limited by junction temperature

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- **Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Parameter ^(note2)	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	60	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{ V}, V_{GS}=0\text{ V}$	--	--	1	μA
Gate–Body Leakage	I_{GSS}	$V_{GS}=\pm 20\text{ V}, V_{DS}=0\text{ V}$	--	--	± 100	nA
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	1	1.4	3	V
Static Drain–Source On–Resistance	$R_{\text{DS}(\text{ON})}$	$V_{GS}=10\text{ V}, I_D=5.5\text{ A}$	--	30	41	mR
		$V_{GS}=4.5\text{ V}, I_D=4.5\text{ A}$	--	35	52	
Input Capacitance	C_{ISS}	$V_{DS}=10\text{ V}, V_{GS}=0\text{ V}, F=1\text{MHz}$	--	1180	--	pF
Output Capacitance	C_{OSS}	--	--	170	--	
Reverse Transfer Capacitance	C_{RSS}	--	--	100	--	
Turn–On Delay Time	$T_{\text{D}(\text{ON})}$	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, R_L=5.4\text{R}, R_{\text{GEN}}=3\text{R}, I_D=5.5\text{A}$	--	--	25	nS
Turn–On Rise Time	T_R	--	--	--	70	
Turn–Off Delay Tim	$T_{\text{D}(\text{OFF})}$	--	--	--	300	
Turn–Off Fall Time	T_F	--	--	--	150	
Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{ V}, I_S=2\text{ A}$	0.5	0.77	1.0	V

1. The value of PD is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{ C}$. The value in any given application depends on the user's specific board design. The current rating is based on the DC thermal resistance rating and PCB layout: A. Minimum footprint; B. With additional heat sink.
2. Repetitive rating, pulse width limited by junction temperature

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- TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

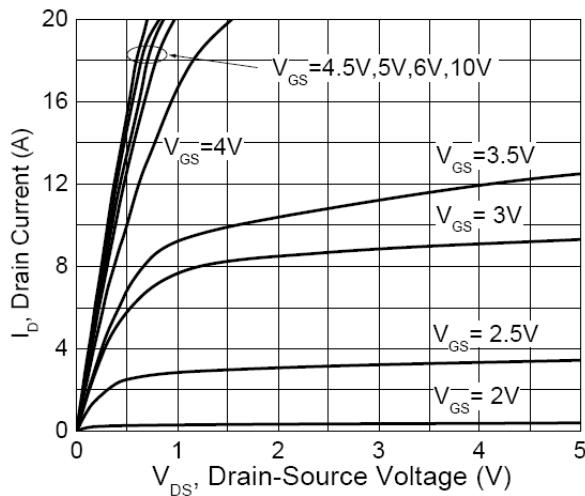


Figure 1. Output Characteristics

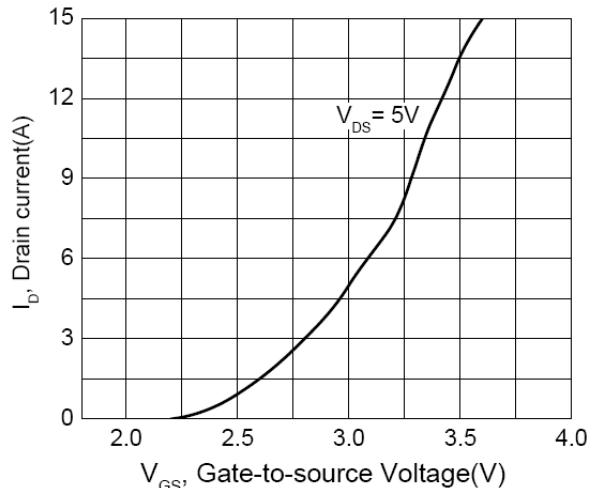


Figure 2. Transfer Characteristics

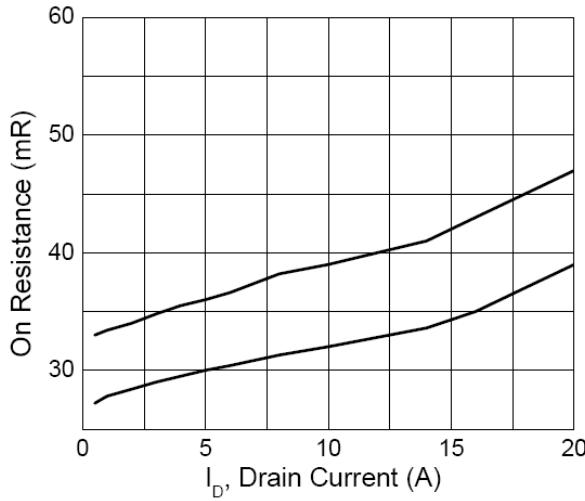


Figure 3. On-Resistance

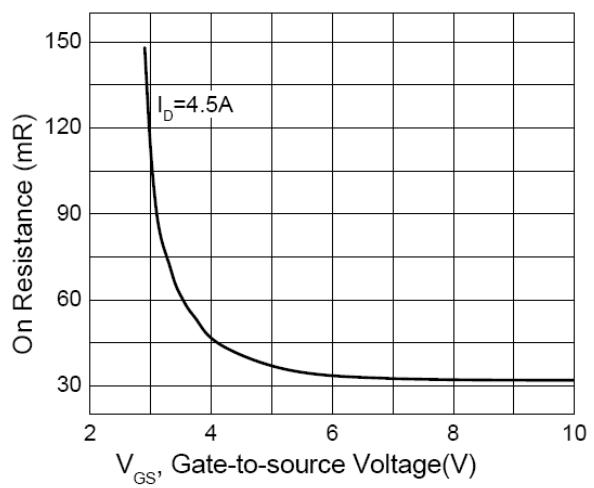


Figure 4. On-Resistance vs. Threshold Voltage

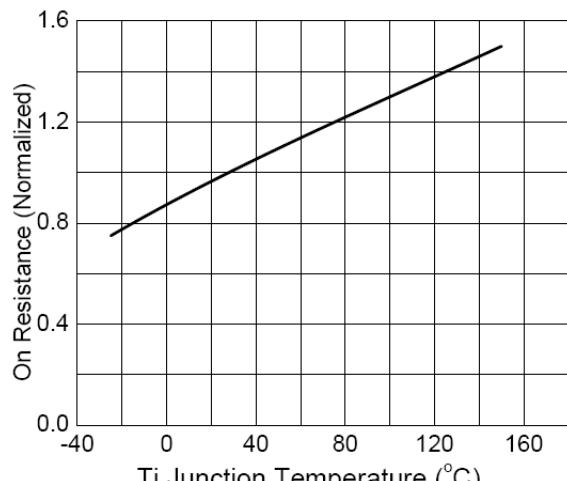


Figure 5 . On-Resistance vs. Temperature

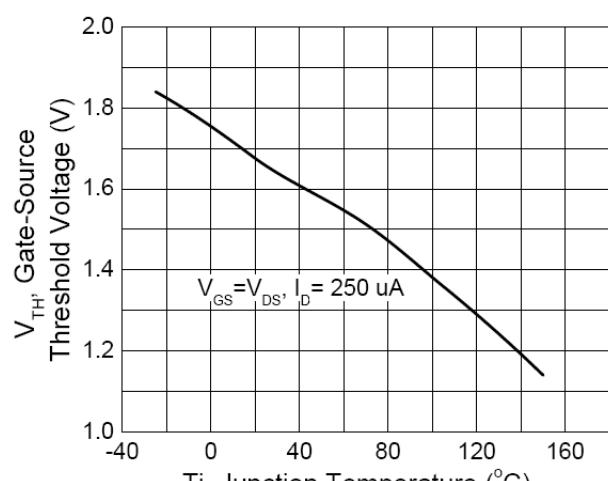
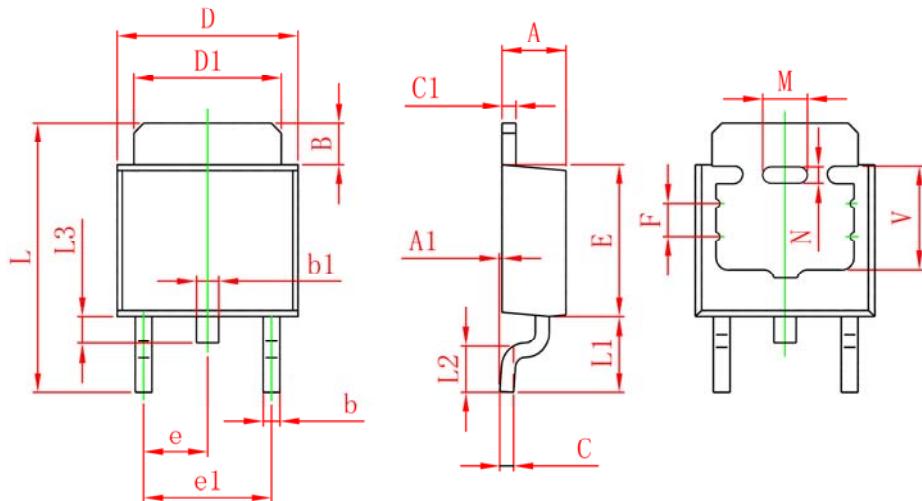


Figure 6. Gate Threshold Vs. Temperature

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- Package Information

TO-252C-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
F	1.200REF.		0.047REF.	
M	1.600REF.		0.063REF.	
N	0.450REF.		0.018REF.	
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF		0.150 REF	